

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. - 9. (cancelled)

10. (original) A method comprising:

fabricating a memory cell of a device, the memory cell comprising a body region doped with charge carriers of a first type, a source region disposed in the body region and doped with charge carriers of a second type, and a drain region disposed in the body region and doped with charge carriers of the second type, wherein the body region, the source region, and the drain region are oriented in a first direction, wherein the body region and the source region form a first junction, wherein the body region and the drain region form a second junction, and wherein a conductivity of the first junction from the body region to the source region in a case that the first junction is unbiased is substantially less than a conductivity of the second junction from the body region to the drain region in a case that the second junction is unbiased;

fabricating a transistor of the device, the transistor oriented in a second direction, wherein the second direction is not parallel to the first direction; and

fabricating a halo implant within the transistor,

wherein a halo implant is not fabricated in the memory cell.

11. (original) A method according to Claim 10, further comprising:

fabricating a conductive element disposed over the body region.

12. (original) A method according to Claim 11, the conductive element to prevent fabrication of a halo implant in the memory cell.

13. (original) A method according to Claim 10, further comprising:

fabricating a second memory cell including a second body region, the second body region and the body region of the memory cell oriented in a direction substantially perpendicular to the first direction.

14. (original) A method according to Claim 13, further comprising:

fabricating a conductive element disposed over the body region and the second body region, the conductive element oriented in the direction.

15. (original) A method according to Claim 14, the conductive element to prevent fabrication of a halo implant in the memory cell.